

IN THE CLAIMS

Please cancel claims 1 - 20 in the application and replace them with new claims 21 - 30 below prior to calculating the filing fee.

21. A process for making a semiconductor device comprising the steps of:
forming a layer of conductive material having a topography that includes a substantially vertical component; and
forming a contact disposed adjacent to and contacting said vertical component.
22. A process as claimed in claim 21 wherein said vertical component defines a localized thick region in the layer of conductive material.
23. A process as claimed in claim 21 wherein said vertical component is a spacer.
24. A process as claimed in claim 21 further comprising the step of forming a structure having an opening therein under said conductive layer and filling said opening with said conductive material to form said vertical component.
25. A process as claimed in claim 21 wherein said conductive layer is a capacitor electrode.
26. A process for making a semiconductor device having an improved contact to a conductive layer comprising the steps of:
providing a first layer of material and forming an opening therein, said opening including sidewalls;
forming a layer of a first conductive material on said first layer of material and along the surfaces of said sidewalls of said opening to form a localized thick region;
forming an overlayer of material on said layer of said first conductive material;
forming a contact hole in said overlayer which communicates with said layer of said first conductive material; and

substantially filling said contact hole in said overlayer with a second conductive material which differs in composition from said first conductive layer and which contacts said first conductive material.

27. A process as claimed in claim 26 in which said first conductive material forms spacers on said sidewalls of said opening.

28. A process as claimed in claim 27 in which said second conductive material contacts at least said spacers.

29. A process as claimed in claim 26 in which said first conductive material comprises polysilicon and said second conductive material comprises a metal.

30. A process as claimed in claim 26 in which said first layer and said overlayer comprise insulating materials.

Respectfully submitted,

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